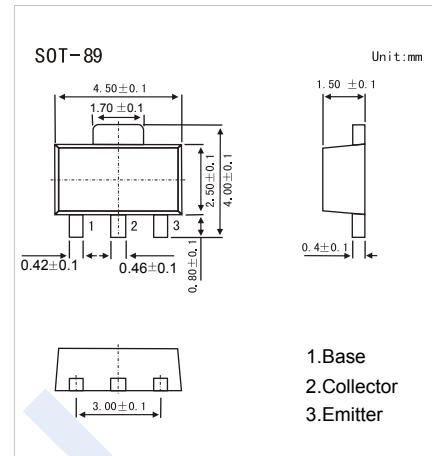


**NPN Transistors****2SC2881****■ Features**

- Small Flat Package
- High Transition Frequency
- High Voltage
- Complementary to 2SA1201

**■ Absolute Maximum Ratings Ta = 25°C**

Parameter	Symbol	Rating	Unit
Collector - Base Voltage	V <sub>CBO</sub>	120	V
Collector - Emitter Voltage	V <sub>C EO</sub>	120	
Emitter - Base Voltage	V <sub>EBO</sub>	5	
Collector Current - Continuous	I <sub>C</sub>	800	mA
Base Current	I <sub>B</sub>	160	
Collector Power Dissipation	P <sub>C</sub>	500	mW
Thermal Resistance From Junction To Ambient	R <sub>θJA</sub>	250	°C/W
Junction Temperature	T <sub>J</sub>	150	°C
Storage Temperature Range	T <sub>stg</sub>	-55 to 150	

**■ Electrical Characteristics Ta = 25°C**

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	V <sub>CBO</sub>	I <sub>C</sub> = 100uA, I <sub>E</sub> = 0	120			V
Collector-emitter breakdown voltage	V <sub>C EO</sub>	I <sub>C</sub> = 10mA, I <sub>B</sub> = 0	120			
Emitter-base breakdown voltage	V <sub>EBO</sub>	I <sub>E</sub> = 100uA, I <sub>C</sub> = 0	5			
Collector-base cut-off current	I <sub>CBO</sub>	V <sub>CB</sub> = 120V, I <sub>E</sub> = 0			0.1	uA
Emitter cut-off current	I <sub>EBO</sub>	V <sub>EB</sub> = 5V, I <sub>C</sub> = 0			0.1	
Collector-emitter saturation voltage	V <sub>C E(sat)</sub>	I <sub>C</sub> =500 mA, I <sub>B</sub> =50mA			1	V
Base-emitter saturation voltage	V <sub>BE(sat)</sub>	I <sub>C</sub> =500 mA, I <sub>B</sub> =50mA			1.2	
Base-emitter voltage	V <sub>BE</sub>	V <sub>C E</sub> = 5V, I <sub>C</sub> = 0.5A			1	
DC current gain	h <sub>FE</sub>	V <sub>C E</sub> = 5V, I <sub>C</sub> = 100mA	80		240	
Collector output capacitance	C <sub>ob</sub>	V <sub>CB</sub> = 10V, I <sub>E</sub> = 0, f=1MHz			30	pF
Transition frequency	f <sub>T</sub>	V <sub>C E</sub> = 5V, I <sub>C</sub> = 100mA			120	MHz

**■ Classification of h<sub>FE</sub>**

Type	2SC2881-O	2SC2881-Y
Range	80-160	120-240
Marking	CO*	CY*

## NPN Transistors

2SC2881

## ■ Typical Characteristics

